ABSTRACT OF THE DISCLOSURE

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A ferroelectric memory capable of suppressing false data reading or the like by increasing a read margin is obtained. This ferroelectric memory comprises a circuit applying a read voltage V_R to a first electrode and a detector capable of detecting the difference between electric capacitances C_{f0} and C_{f1} of a ferroelectric film when the potential difference of a second electrode corresponding to the difference between the electric capacitances C_{f0} and C_{f1} of the ferroelectric film is in excess of a detection limit voltage V_S . The electric capacitance C_2 of the second electrode is set to satisfy the following expression:

$$C_{f0} < C_2 \le 1/2 \times \{(C_{f1} - C_{f0})V_R/V_S - (C_{f1} + C_{f0})\}$$